PROCESS CP191V

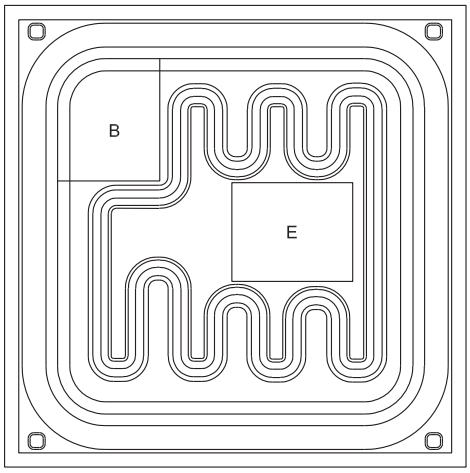
Small Signal Transistor

NPN - Amp/Switch Transistor Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	16.5 x 16.5 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.5 x 4.3 MILS
Emitter Bonding Pad Area	3.5 x 4.3 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 13,000Å

GEOMETRY



BACKSIDE COLLECTOR R3

GROSS DIE PER 4 INCH WAFER
41,699

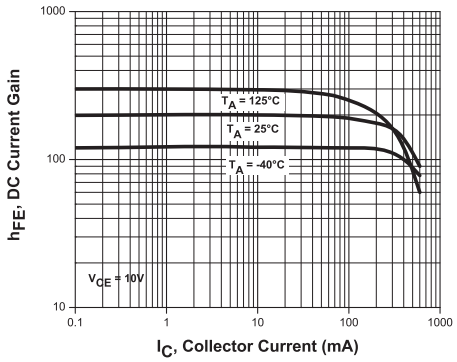
PRINCIPAL DEVICE TYPES
CMLT2222A
CMLT2207
CMLM2205
CMKT2207

R1 (22-March 2010)

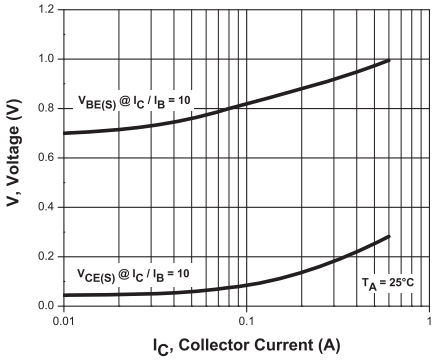
PROCESS CP191V

Typical Electrical Characteristics

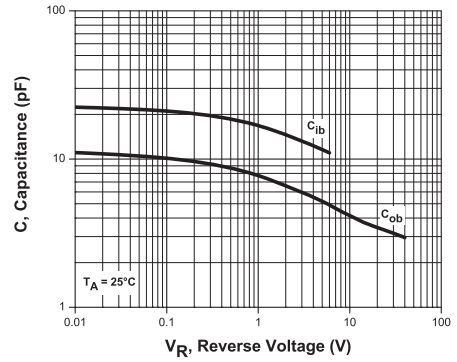
DC Current Gain



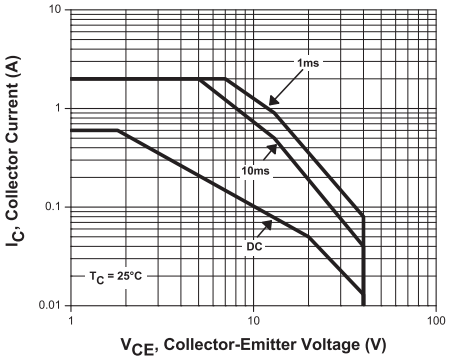
"ON" Voltage



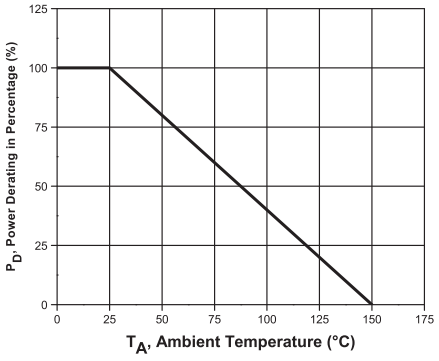
Capacitance



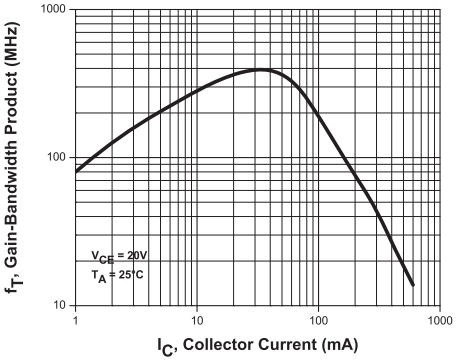
Safe Operating Area



Normalized Power Derating



Current Gain-Bandwidth Product



R1 (22-March 2010)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES

PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

CONTACT US

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